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	Applicant(s): Hiroshi KUDO et al.	
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U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
AA						
AB						
AC						
AD						
AE						

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Country	Translation (Yes or No)
CAI	AF 11-251595	09/17/1999	Japan	Yes (Abstract Only), see page 2 in the spec.
CAI	AG 11-261063	09/24/1999	Japan	Yes (Abstract Only), see page 2 in the spec.
CAI	AH 2001-024187	01/26/2001	Japan	Yes (Abstract Only), see page 2 in the spec.
CAI	AI 2001-274379	10/05/2001	Japan	Yes (Abstract Only), see pages 2 and 52 in the spec.
CAI	AJ 10-125677	05/15/1998	Japan	Yes (Abstract Only)

OTHER DOCUMENTS

CAI	AK	Murarka, S. P., "Silicides for VLSI Applications", Academic Press, Inc., pp. 88~95, 1983, (see pages 3 and 44 in the spec.)
CAI	AL	Qin M. et al., "Investigation of Polycrystalline Nickel Silicide films as a Gate Material", Journal of The Electrochemical Society, 148 (5) (The Electrochemical Society, Inc.), pp. G271~G274 (2001) (see pages 3 and 49 in the spec.)
Examiner		Date Considered 2/16/2005